

Silicon PNP Power Transistors

2SB1367

DESCRIPTION

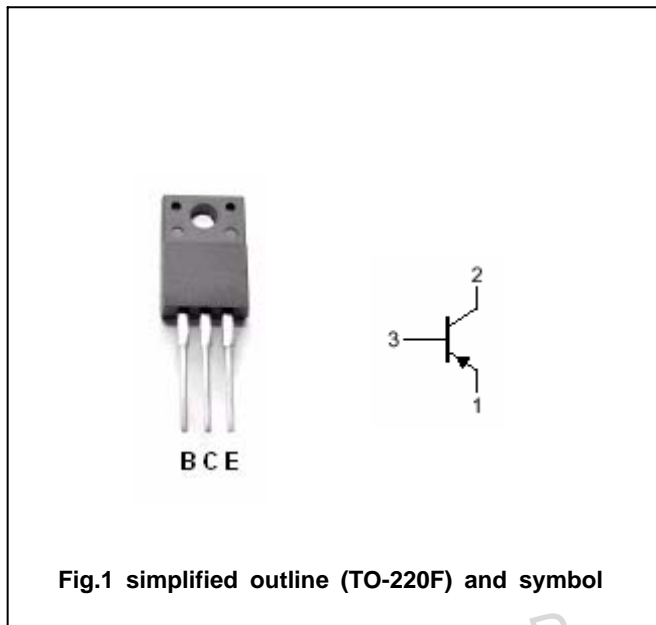
- With TO-220F package
- Complement to type 2SD2059
- Low collector saturation voltage:  
 $V_{CE(sat)} = -2.0V(\text{Max})$  at  $I_C = -4A, I_B = -0.4A$
- Collector power dissipation:  
 $P_C = 30W(T_C = 25^\circ\text{C})$

APPLICATIONS

- With general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings (Ta=25 °C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector-emitter voltage	Open base	-100	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-5	A
$I_B$	Base current		-0.5	A
$P_C$	Collector dissipation	$T_C = 25$	30	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

## Silicon PNP Power Transistors

2SB1367

## CHARACTERISTICS

 $T_j=25$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-100			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=-4A; I_B=-0.4A$			-2.0	V
$V_{BE}$	Base-emitter on voltage	$I_C=-4A; V_{CE}=-5V$			-1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=-100V; I_E=0$			-0.1	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-1.0	mA
$h_{FE-1}$	DC current gain	$I_C=-1A; V_{CE}=-5V$	40		240	
$h_{FE-2}$	DC current gain	$I_C=-4A; V_{CE}=-5V$	20			
$f_T$	Transition frequency	$I_C=-1A; V_{CE}=-5V$		5.0		MHz
$C_{OB}$	Collector output capacitance	$f=1MHz; V_{CB}=-10V$		270		pF

◆  $h_{FE-1}$  Classifications

R	O	Y
40-80	70-140	120-240

Silicon PNP Power Transistors

2SB1367

PACKAGE OUTLINE

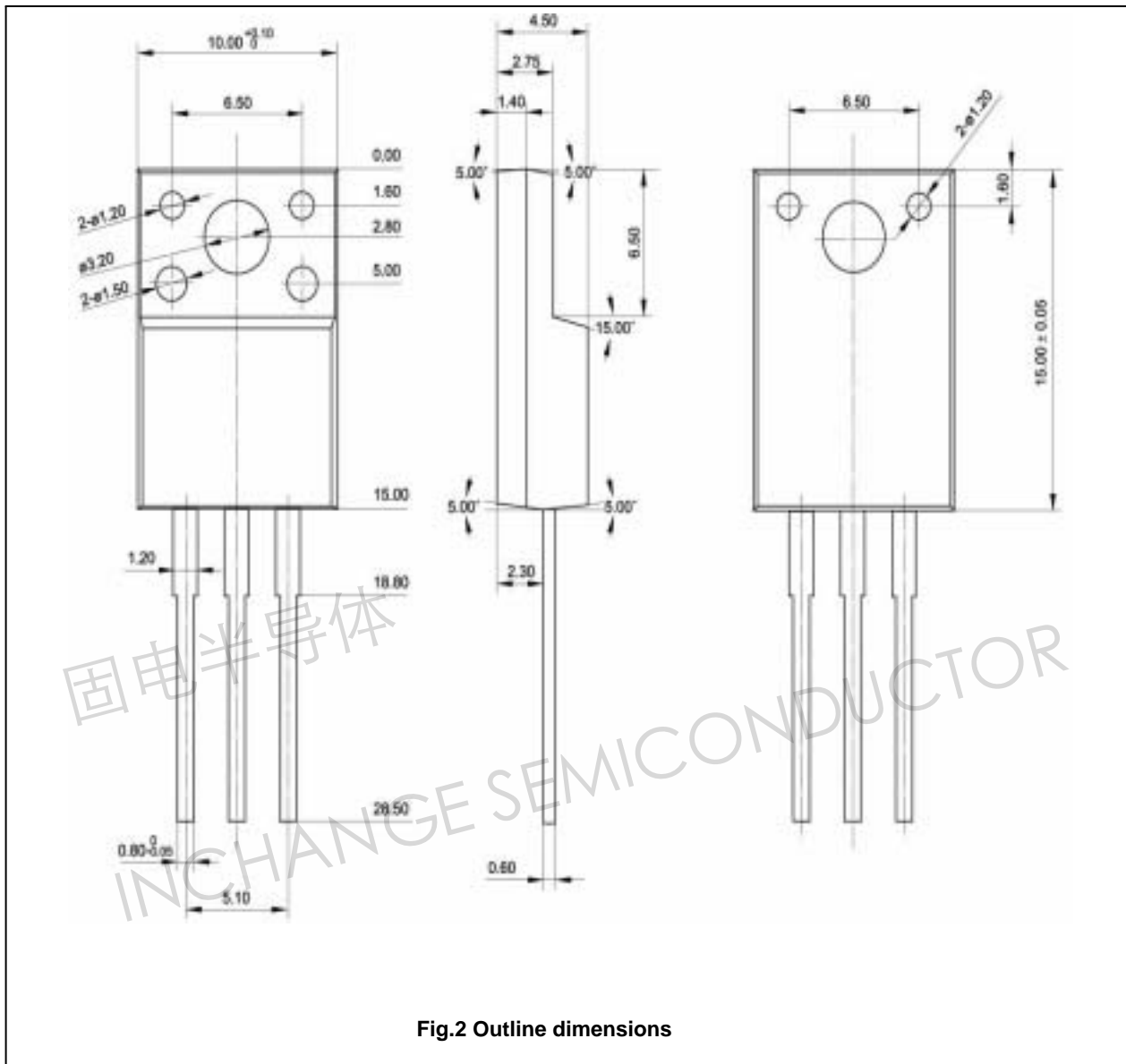


Fig.2 Outline dimensions

Silicon PNP Power Transistors

2SB1367

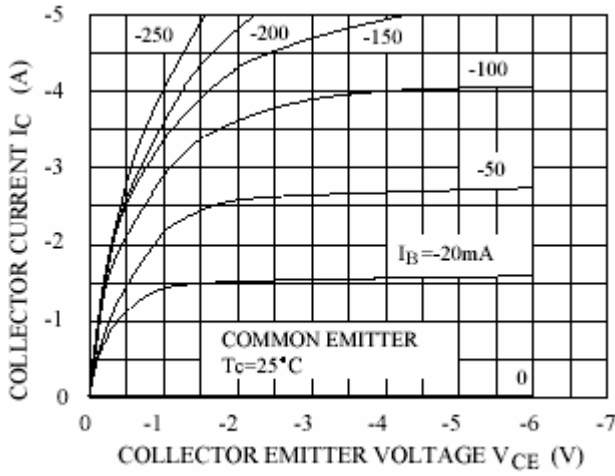


Fig.3 Static Characteristic

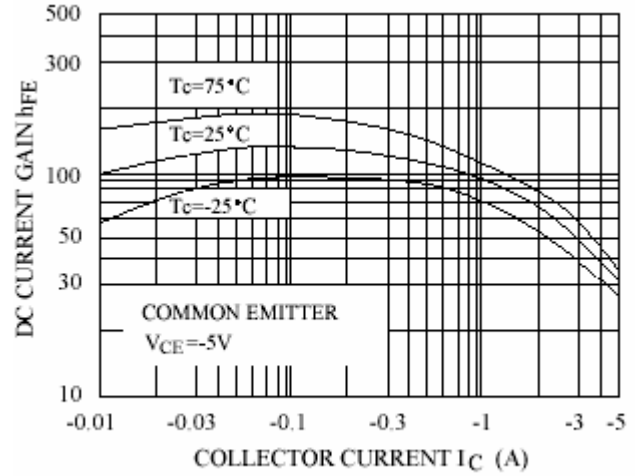


Fig.4 DC current Gain

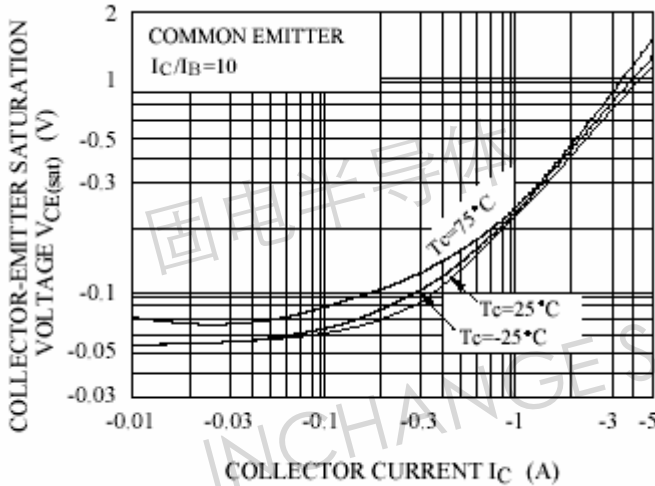


Fig.5 Collector-Emitter Saturation Voltage

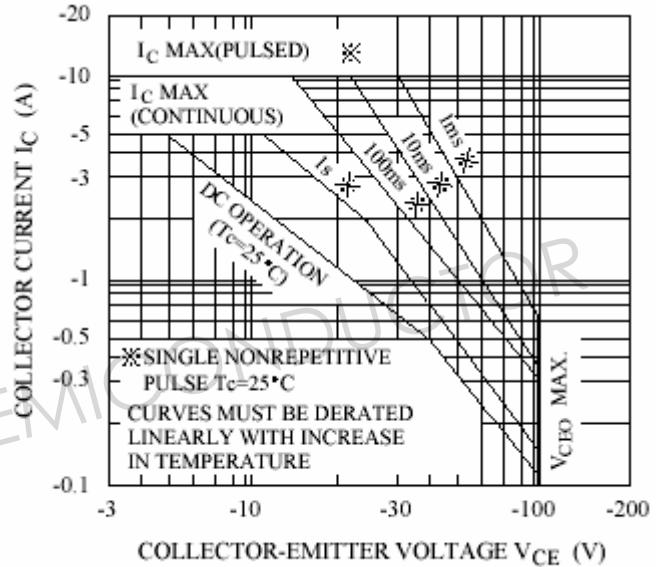


Fig.6 Safe Operating Area